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(54) **Title:** AN SOI DEVICE HAVING A SUBSTRATE DIODE WITH PROCESS TOLERANT CONFIGURATION AND METHOD OF FORMING THE SOI DEVICE

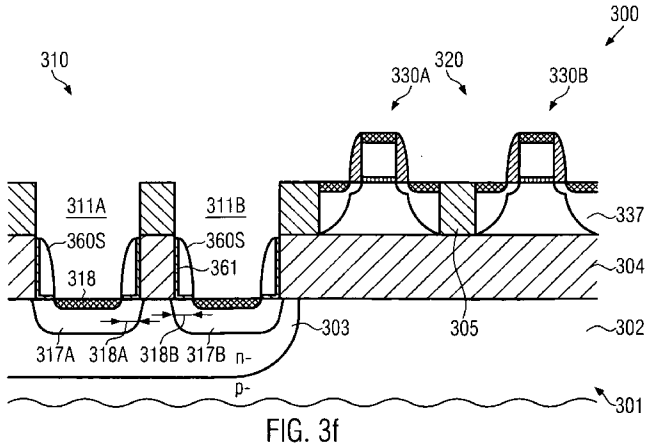


FIG. 3f

(57) **Abstract:** A substrate diode for an SOI device (200, 300) is formed in accordance with an appropriately designed manufacturing flow, wherein transistor performance enhancing mechanisms may be implemented substantially without affecting the diode characteristics. In one aspect, respective openings (211A, 211B, 311A, 311B) for the substrate diode may be formed after the formation of a corresponding sidewall spacer structure (236, 336) used for defining the drain and source regions (237, 337), thereby obtaining a significant lateral distribution of the dopants in the diode areas, which may therefore provide sufficient process margins during a subsequent silicidation sequence on the basis of a removal of the spacers (236, 336) in the transistor devices (230A, 230B, 330A, 330B). In a further aspect, in addition to or alternatively, an offset spacer (360S) may be formed substantially without affecting the configuration of respective transistor devices (230A, 230B, 330A, 330B).

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